BEST AVAILABLE COPY

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-2. (canceled)

3. **(currently amended)** The method as claimed in claim [[1]] 8, wherein the first passivating gas is H_2 or N_2.

4. (original) The method as claimed in claim 3, wherein the second passivating gas is H_2O or NH_3.

5. **(currently amended)** The method as claimed in claim [[1]] 8, wherein the first type of transistors are PMOS transistors and the second type of transistors are NMOS transistors.

6-7. (canceled)

8. (previously presented) A method of passivating a semiconductor device, said method comprising:

placing a semiconductor device in a chamber, the semiconductor device having a first type of transistors and a second type of transistors;

introducing a first passivating gas and a second passivating gas into the chamber; and

heating the semiconductor device to a temperature for a period sufficient to passivate the semiconductor device;

BEST AVAILABLE COPY

wherein

the first passivating gas is introduced into the chamber and the semiconductor device is heated to a temperature for a period sufficient to passivate the first type of transistors, and then the second passivating gas is introduced into the chamber and the semiconductor device is heated to a temperature for a period sufficient to passivate the second type of transistors; and

the first passivating gas is drained out of the chamber by introducing the second passivating gas into the chamber and the pressure of the chamber is greater than 1 atmosphere.

9. **(currently amended)** The method as claimed in claim [[1]] 8, wherein the semiconductor device comprises a CMOS circuit of an active matrix display device.

10. **(currently amended)** The method as claimed in claim [[1]] 8, wherein the chamber maintains a pressure between 5 atmospheres and 20 atmospheres.

11. **(currently amended)** The method as claimed in claim [[1]] 8, wherein the first type of transistors are PMOS transistors and the first passivating gas is H_2 or N_2, and the second type of transistors are NMOS transistors and the second passivating gas is H_2O or NH_3.

12-21. (canceled)